

20V N-Channel Enhancement Mode MOSFET

Description

The UCB2302 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 20V$ $I_D = 2.8A$

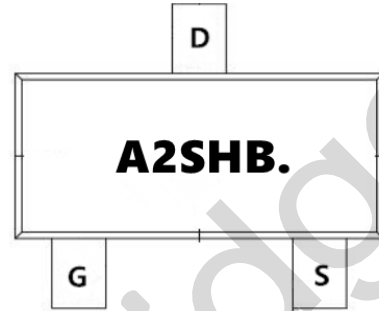
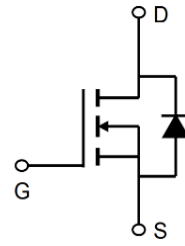
$R_{DS(ON)} < 55m\Omega$ @ $V_{GS}=10V$ (Type: 48m Ω)

Application

Battery protection

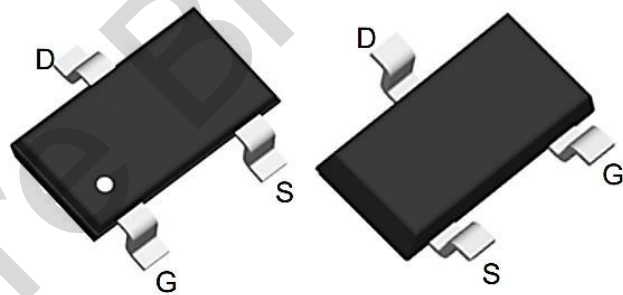
Load switch

Uninterruptible power suppl



Top View

Bottom View



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
UCB2302	SOT23L	A2SHB	3000

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	2.8	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	1.6	A
I_{DM}	Pulsed Drain Current ²	7.4	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ³	0.9	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	90	$^\circ C/W$

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu\text{A}$	20	22	-	V
IDSS	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V,$	-	-	1.0	μA
IGSS	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	± 100	nA
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.4	0.6	1.2	V
RDS(on)	Static Drain-Source on-Resistance note2	$V_{GS}=4.5V, I_D=2A$	-	42	50	m Ω
		$V_{GS}=2.5V, I_D=1.5A$	-	54	70	
C _{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V, f=1.0\text{MHz}$	-	184	-	pF
C _{oss}	Output Capacitance		-	38	-	pF
C _{rss}	Reverse Transfer Capacitance		-	28	-	pF
Q _g	Total Gate Charge	$V_{DS}=10V, I_D=3A, V_{GS}=4.5V$	-	2.7	-	nC
Q _{gs}	Gate-Source Charge		-	0.4	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	0.5	-	nC
td(on)	Turn-on Delay Time	$V_{DS}=10V, I_D=3A, R_{GEN}=3\Omega, V_{GS}=4.5V$	-	2.3	-	ns
t _r	Turn-on Rise Time		-	3.1	-	ns
td(off)	Turn-off Delay Time		-	9.2	-	ns
t _f	Turn-off Fall Time		-	2.5	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	3	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	12	A
VSD	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=3A$	-	-	1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

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Typical Characteristics

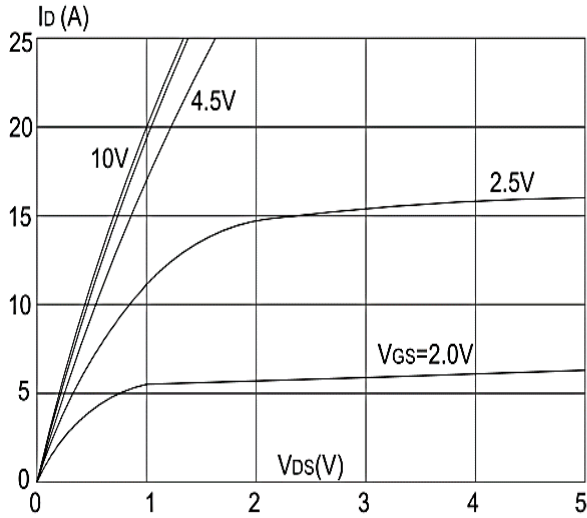


Figure 1: Output Characteristics

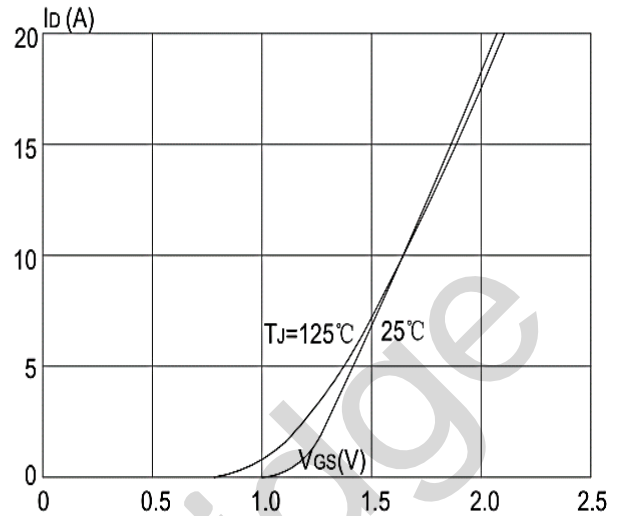


Figure 2: Typical Transfer Characteristics

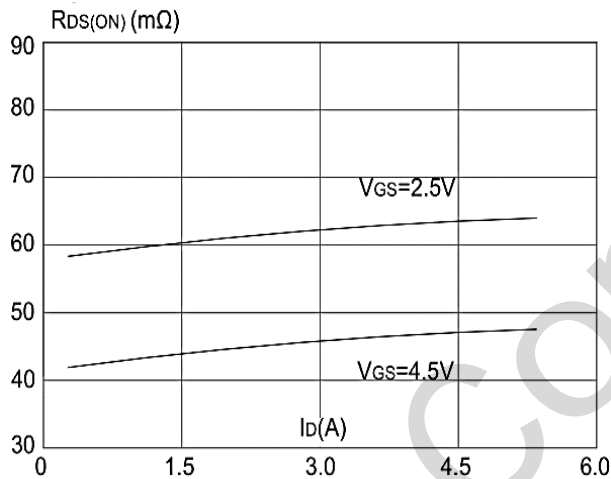


Figure 3: On-resistance vs. Drain Current

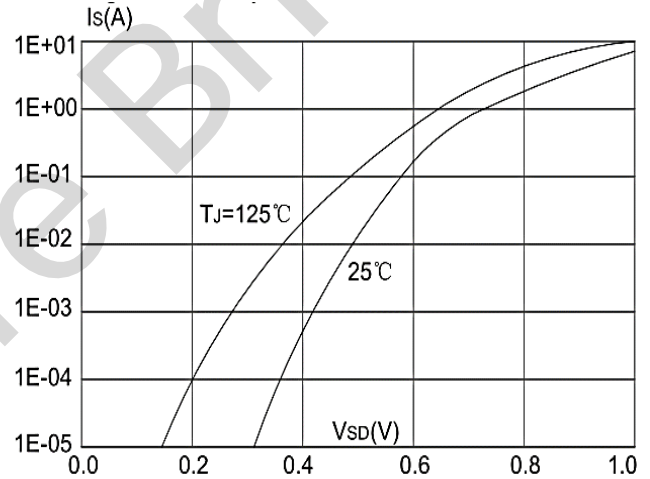


Figure 4: Body Diode Characteristics

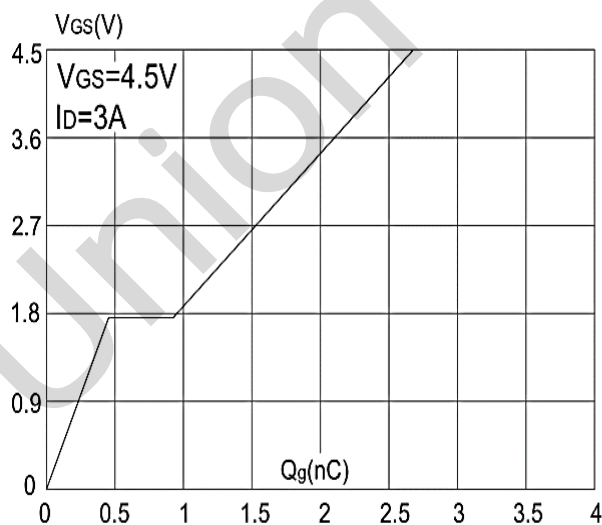


Figure 5: Gate Charge Characteristics

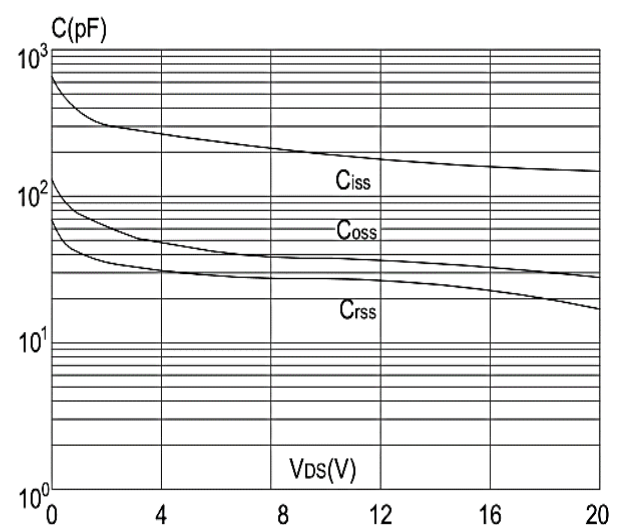


Figure 6: Capacitance Characteristics

20V N-Channel Enhancement Mode MOSFET

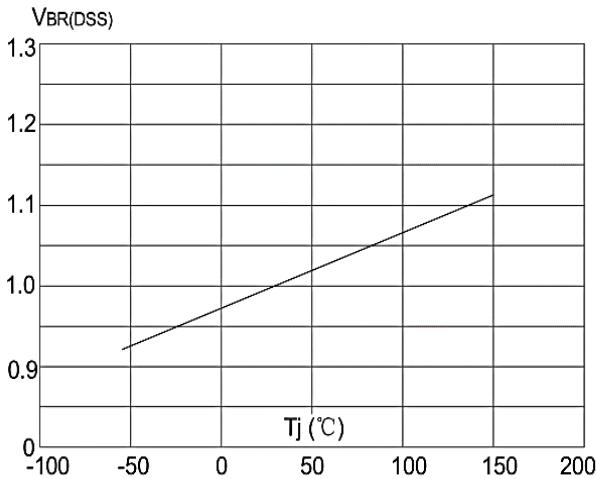


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

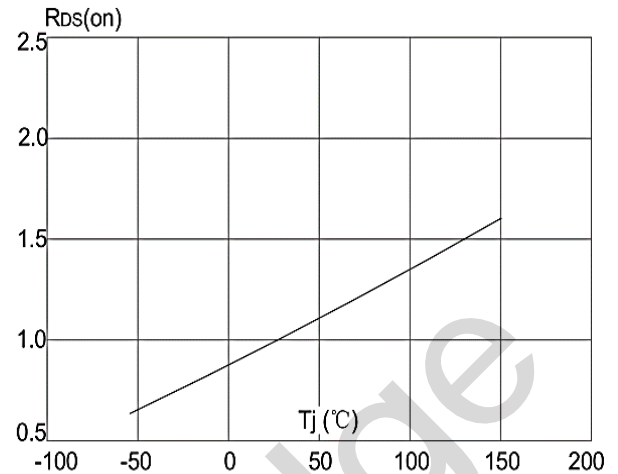


Figure 8: Normalized on Resistance vs. Junction Temperature

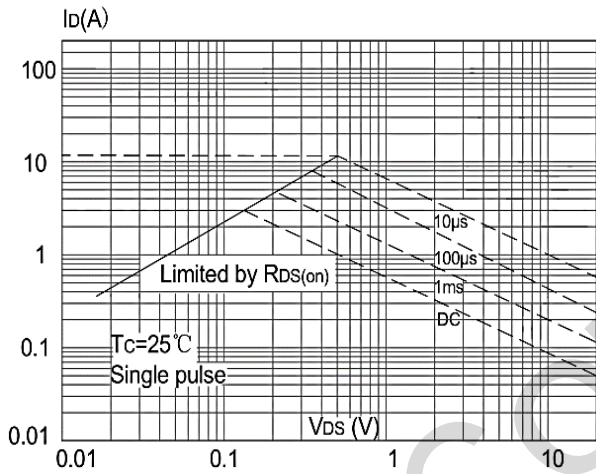


Figure 9: Maximum Safe Operating Area

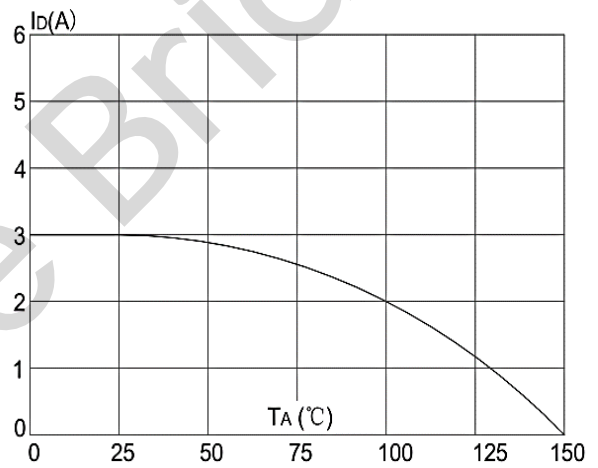


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

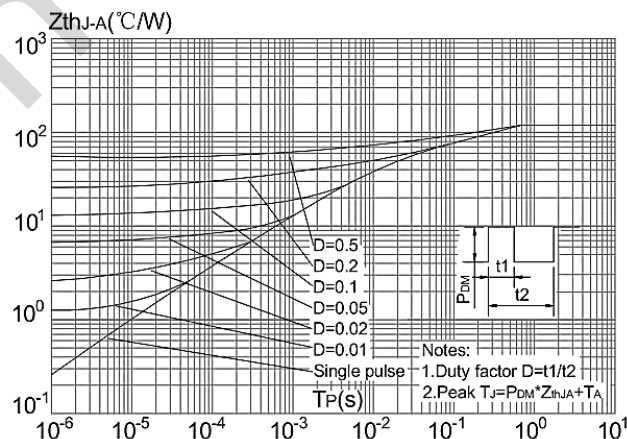
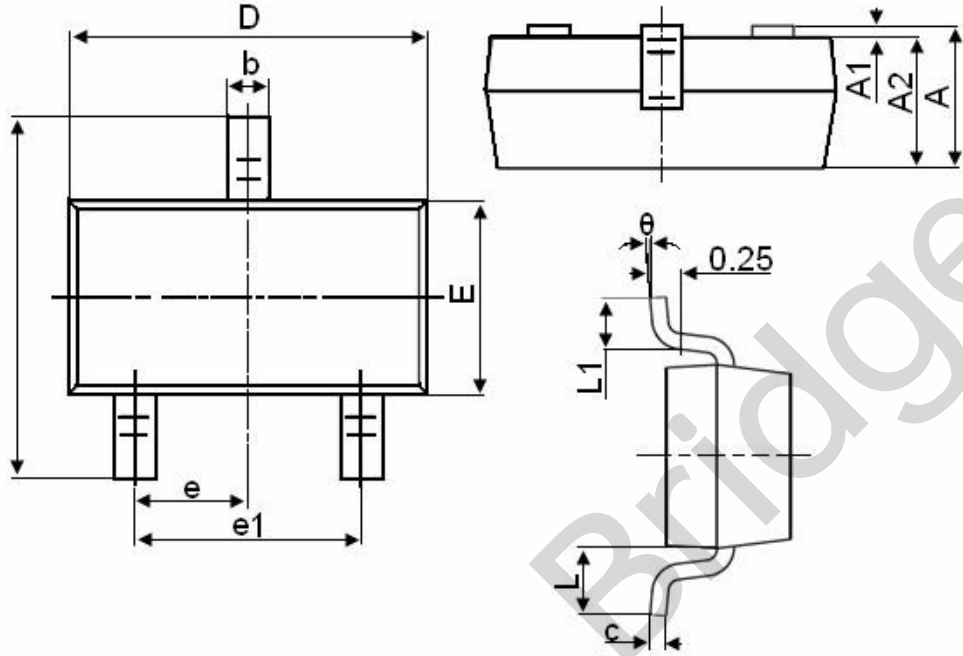


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambien

Package Mechanical Data-SOT23-XC-Single



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°